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insulation layer on a substrate;

treating the completely formed silicon oxycarbide layer with plasma; and

stacking photoresist on the plasma-treated oxycarbide layer and patterning the resultant structure.

11. (Three Times Amended) A method of fabricating a semiconductor device having a low dielectric interlayer insulation layer, comprising:

stacking a completely formed silicon oxycarbide layer (SiOC) as the low dielectric interlayer insulation layer on a substrate;

treating the completely formed silicon oxycarbide layer with plasma; and

forming an interconnection at the silicon oxycarbide layer using a damascene process.

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